

IRL3502SPbF

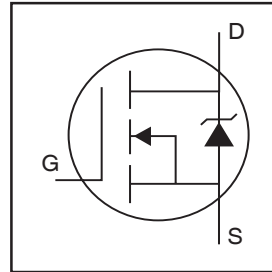
HEXFET® Power MOSFET

- Advanced Process Technology
- Surface Mount
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching
- Lead-Free

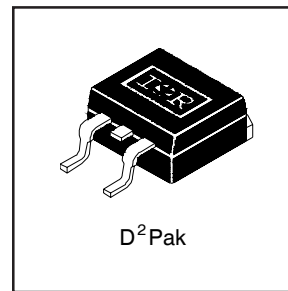
Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters in the PC environment. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



$V_{DSS} = 20V$
$R_{DS(on)} = 0.007\Omega$
$I_D = 110A\text{⑥}$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V\text{⑤}$	110⑥	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V\text{⑤}$	67	
I_{DM}	Pulsed Drain Current ① ⑤	420	
$P_D @ T_C = 25^\circ C$	Power Dissipation	140	W
	Linear Derating Factor	1.1	W/°C
V_{GS}	Gate-to-Source Voltage	± 10	V
V_{GSM}	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu s$)	14	V
E_{AS}	Single Pulse Avalanche Energy② ⑤	390	mJ
I_{AR}	Avalanche Current①	64	A
E_{AR}	Repetitive Avalanche Energy①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑤	5.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.89	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	—	40	

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/°C	Reference to 25°C , $I_D = 1.0\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.008	Ω	$V_{GS} = 4.5V, I_D = 64A$ ④
		—	—	0.007		$V_{GS} = 7.0V, I_D = 64A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	77	—	—	S	$V_{DS} = 10V, I_D = 64A$ ⑤
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 10V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -10V$
Q_g	Total Gate Charge	—	—	110	nC	$I_D = 64A$
Q_{gs}	Gate-to-Source Charge	—	—	27		$V_{DS} = 16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	39		$V_{GS} = 4.5V$, See Fig. 6 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	140	—		$I_D = 64A$
$t_{d(off)}$	Turn-Off Delay Time	—	96	—		$R_G = 3.8\Omega, V_{GS} = 4.5V$
t_f	Fall Time	—	130	—		$R_D = 0.15\Omega$, ④⑤
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	4700	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1900	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	640	—		$f = 1.0\text{MHz}$, See Fig. 5⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①⑤	—	—	420		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 64A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	87	130	ns	$T_J = 25^\circ\text{C}, I_F = 64A$
Q_{rr}	Reverse Recovery Charge	—	200	310	nC	$di/dt = 100A/\mu s$ ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 190\mu H$
 $R_G = 25\Omega, I_{AS} = 64A$.
- ③ $I_{SD} \leq 64A$, $di/dt \leq 86A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ Uses IRL3502 data and test conditions
- ⑥ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4

** When mounted on FR-4 board using minimum recommended footprint.
For recommended footprint and soldering techniques refer to application note #AN-994.

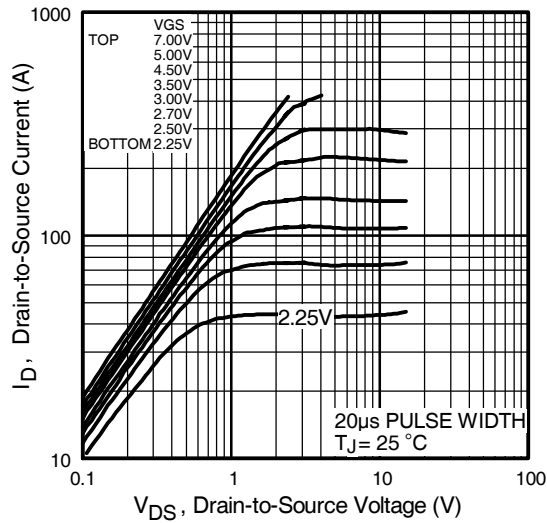


Fig 1. Typical Output Characteristics

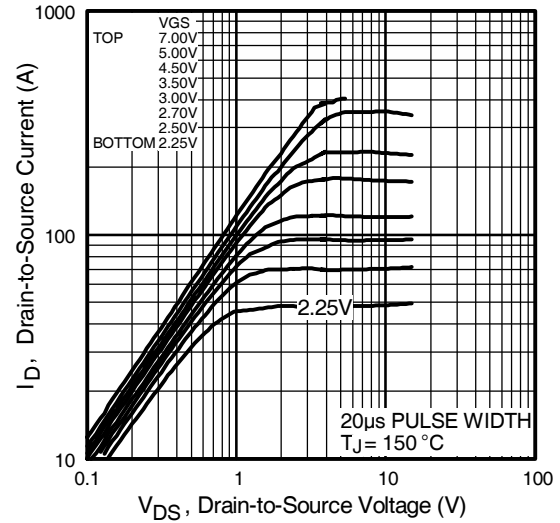


Fig 2. Typical Output Characteristics

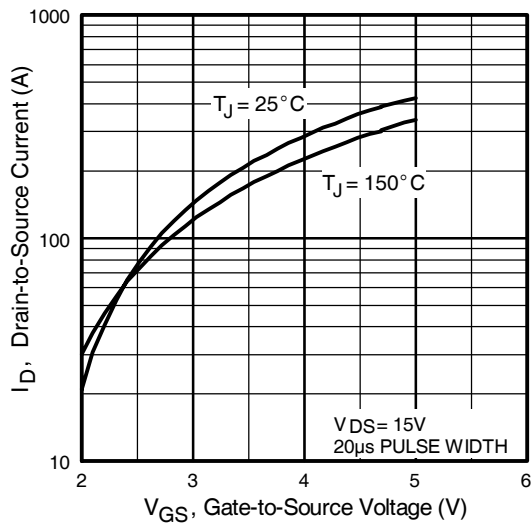


Fig 3. Typical Transfer Characteristics

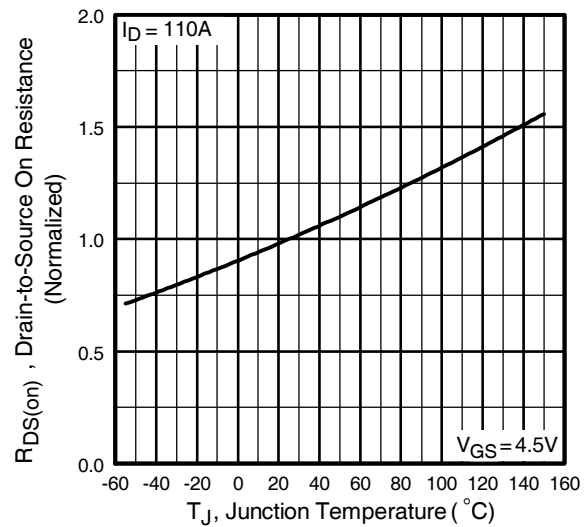


Fig 4. Normalized On-Resistance Vs. Temperature

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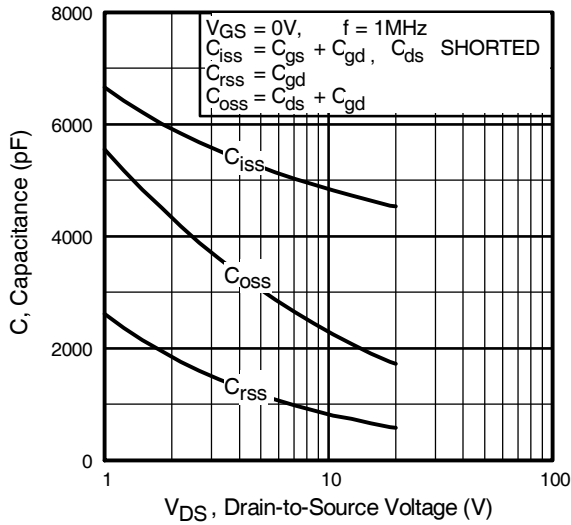


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

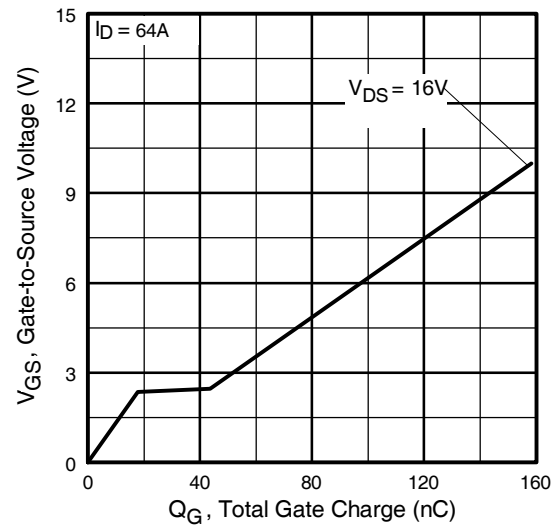


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

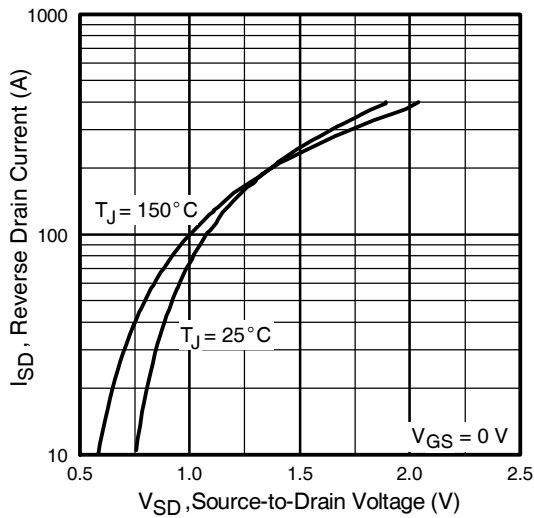


Fig 7. Typical Source-Drain Diode Forward Voltage

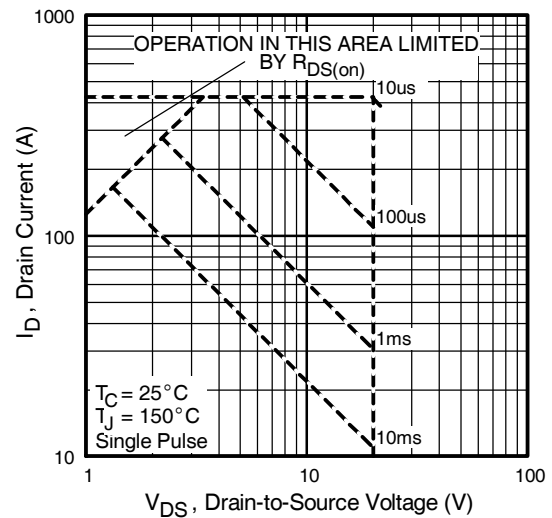


Fig 8. Maximum Safe Operating Area

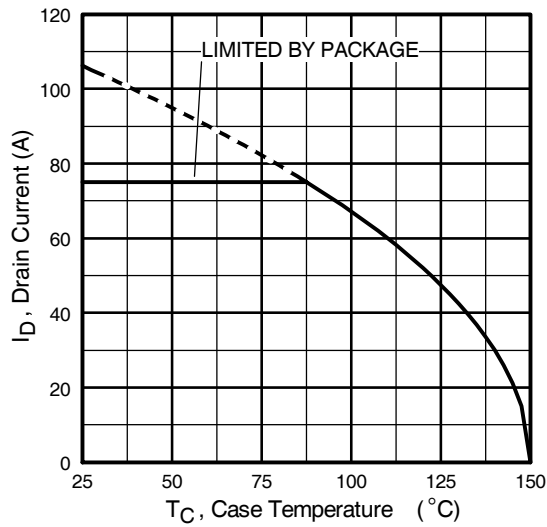


Fig 9. Maximum Drain Current Vs. Case Temperature

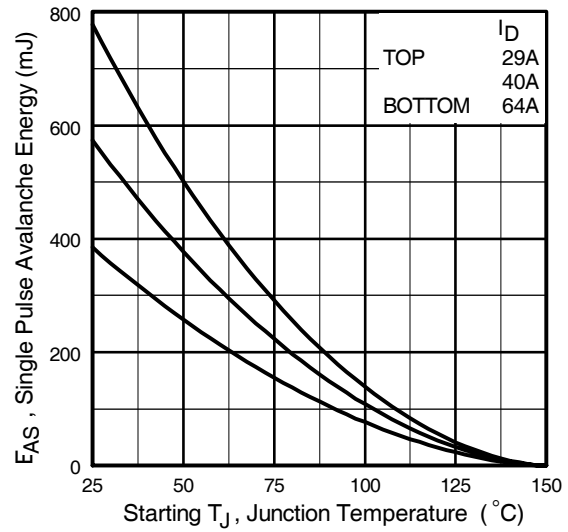


Fig 10. Maximum Avalanche Energy Vs. Drain Current

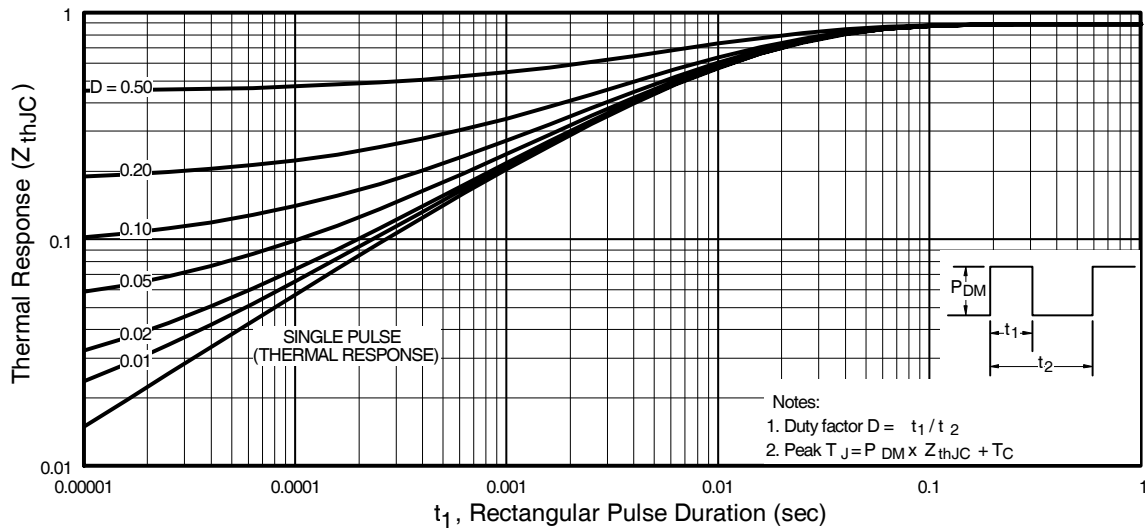


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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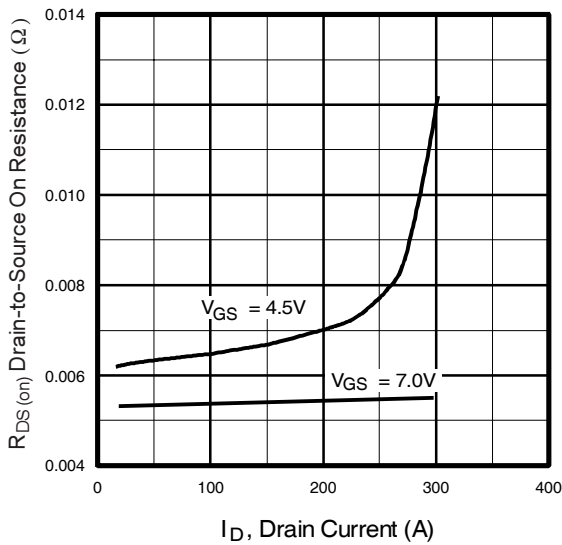


Fig 12. On-Resistance Vs. Drain Current

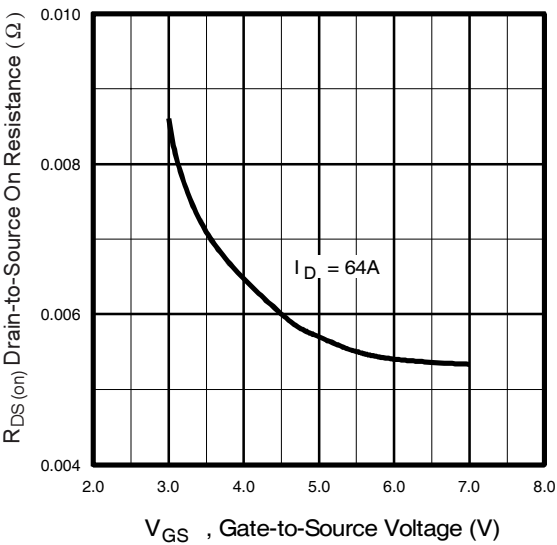
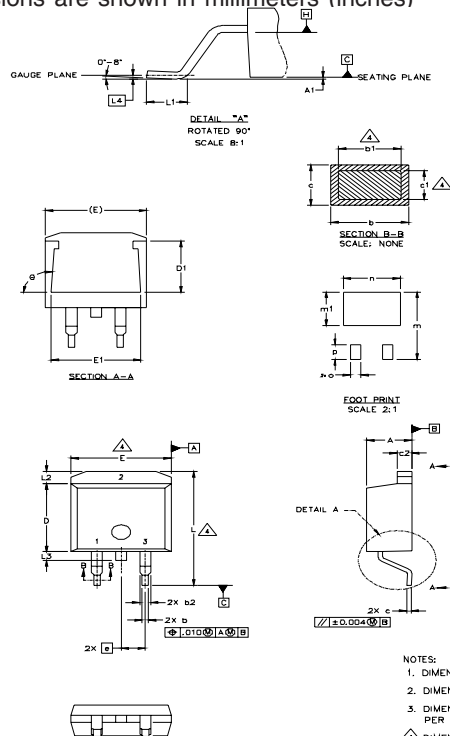


Fig 13. On-Resistance Vs. Gate Voltage

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
ø	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

NOTES:

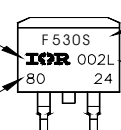
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

D²Pak Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead-Free"

INTERNATIONAL
RECTIFIER
LOGO

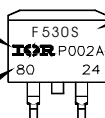


PART NUMBER

DATE CODE
YEAR 0 = 2000
WEEK 02
LINE L

OR

INTERNATIONAL
RECTIFIER
LOGO



PART NUMBER

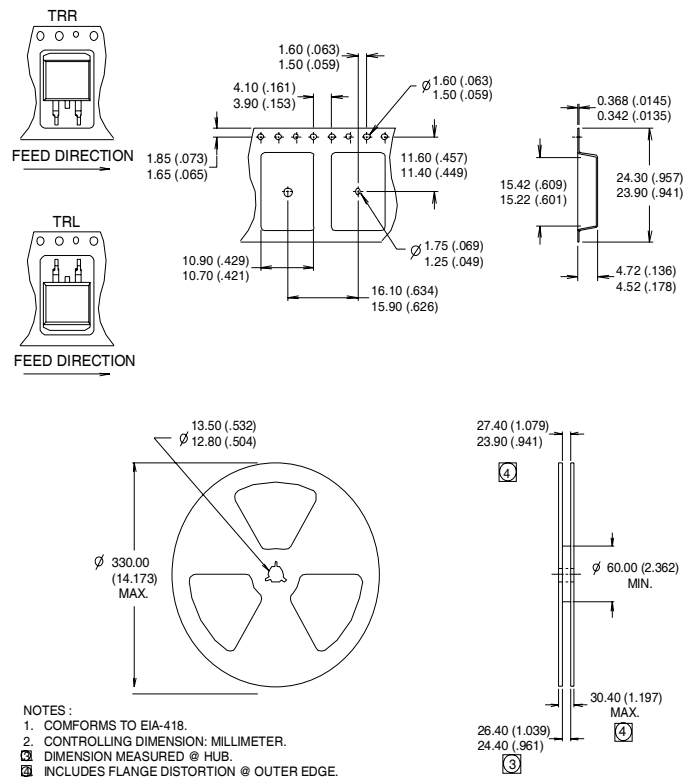
DATE CODE
P = DESIGNATES LEAD-FREE
PRODUCT (OPTIONAL)
YEAR 0 = 2000
WEEK 02
A = ASSEMBLY SITE CODE

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D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.03/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>